CZT5401 TRANSISTOR (PNP)

1.BASE
2.COLLECTOR
3.EMITTER

SOT-223

FEATURES

- High Voltage
- High Voltage Amplifier Application

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-600	mA
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-0.1mA,I_E=0	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-120V,I_E=0			-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V,I_C=0			-50	nA
DC current gain	$h_{FE(1)}$	V_{CE}=-5V, I_C=-1mA	50			
	$h_{FE(2)}$	V_{CE}=-5V, I_C=-10mA	100		300	
	$h_{FE(3)}$	V_{CE}=-5V, I_C=-50mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA,I_B=-1mA			-0.2	V
		I_C=-50mA,I_B=-5mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-10mA,I_B=-1mA			-1	V
		I_C=-50mA,I_B=-5mA			-1	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-10mA, f=100MHz	100		300	MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz			6	pF